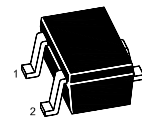


MMBTSC3356W

NPN Silicon Epitaxial Planar Transistor

for microwave low noise amplifier at VHF, UHF and CATV band.

The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	20	V
Collector Emitter Voltage	V_{CEO}	12	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_{amb} = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$ Current Gain Group	Q h_{FE}	50	-	100	-
	R h_{FE}	80	-	160	-
	S h_{FE}	125	-	250	-
Collector Cutoff Current at $V_{CB} = 10\text{ V}$	I_{CBO}	-	-	1	μA
Emitter Cutoff Current at $V_{EB} = 1\text{ V}$	I_{EBO}	-	-	1	μA
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$	f_T	-	7	-	GHz
Feed-Back Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	$C_{re}^{1)}$	-	0.55	1	pF
Insertion Power Gain at $V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$, $f = 1\text{ GHz}$	$ S_{21e} ^2$	-	11.5	-	dB
Noise Figure at $V_{CE} = 10\text{ V}$, $I_C = 7\text{ mA}$, $f = 1\text{ GHz}$	NF	-	1.1	2	dB

¹⁾ The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

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TYPICAL CHARACTERISTICS (T_A = 25 °C)

